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Medium Power Phase Control Thyristors (Stud Version), 50 A



PRODUCT SUMMARY			
Package	TO-208AC (TO-65)		
Diode variation	Single SCR		
I _{T(AV)}	50 A		
V _{DRM} /V _{RRM}	100 V to 1200 V		
V _{TM}	1.60 V		
I _{GT}	100 mA		
TJ	-40 °C to 125 °C		

FEATURES

- High current rating
- Excellent dynamic characteristics
- $dV/dt = 1000 V/\mu s$ option
- Superior surge capabilities
- Standard package
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- · Phase control applications in converters
- Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I		50	A		
I _{T(AV)}	T _C	94	°C		
I _{T(RMS)}		80	A		
I _{TSM}	50 Hz	1430	٨		
	60 Hz	1490	A		
l ² t	50 Hz	10.18	kA ² s		
1-1	60 Hz	9.30	KA-5		
V _{DRM} /V _{RRM}		100 to 1200	V		
t _q	Typical	110	μs		
TJ		-40 to 125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA			
	10	100	150				
	20	200	300				
	40	400	500				
VS-50RIA	60	600	700	15			
	80	800	900				
	100	1000	1100				
	120	1200	1300				

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs ⁽²⁾ For voltage pulses with $t_p \le 5$ ms

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ABSOLUTE MAXIMUM RATI	NGS					
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	l=res	180° sinusoi	180° sinusoidal conduction		50	А
at case temperature	I _{T(AV)}				94	°C
Maximum RMS on-state current	I _{T(RMS)}				80	А
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		1490	Α
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{BBM}		1200	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1255	
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	10.18	kA ² s
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		9.30	
	14t	t = 10 ms	100 % V _{RRM} reapplied		7.20	
		t = 8.3 ms			6.56	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied, T _J = T _J maximum		101.8	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $ _{T(AV)}$ < l < π x $ _{T(AV)}$), T _J = T _J maximum		0.94	v	
High level value of threshold voltage	V _{T(TO)2}	(π x I _{T(AV)} < I	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.08	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)}), T _J = T _J maximum		4.08	mΩ	
High level value of on-state slope resistance	r _{t2}	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ 3.34		3.34	11152	
Maximum on-state voltage	V _{TM}	I _{pk} = 157 A, T _J = 25 °C		1.60	V	
Maximum holding current	I _H	T_{J} = 25 °C, anode supply 22 V, resistive load, initial I_{T} = 2 A		200	mA	
Latching current	١ _L	Anode supp	oly 6 V, resistive lo	ad	400	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum rate of	$V_{DRM} \leq 600 \ V$	dl/dt	$T_{C} = 125 \text{ °C}, V_{DM} = \text{Rated } V_{DRM},$	200	A/us
rise of turned-on current	$V_{\text{DRM}} \le 1600 \text{ V}$ $U_{\text{TM}} = (2 \text{ x rated dl/dt}) \text{ A}$		Gate pulse = 20 V, 15 $\Omega,$ t_p = 6 $\mu s,$ t_r = 0.1 μs maximum I_{TM} = (2 x rated dl/dt) A	100	λγμs
Typical delay time		t _d	$t_{d} \qquad \begin{array}{c} T_{C} = 25 \ ^{\circ}\text{C}, \ V_{DM} = \text{Rated} \ V_{DRM}, \ I_{TM} = 10 \ \text{A} \ \text{dc} \ \text{resistive circuit} \\ \text{Gate pulse} = 10 \ \text{V}, \ 15 \ \Omega \ \text{source}, \ t_{p} = 20 \ \mu\text{s} \end{array}$		
Typical turn-off time		tq	T _C = 125 °C, I_{TM} = 50 A, reapplied dV/dt = 20 V/µs dIr/dt = - 10 A/µs, V _R = 50 V		μs

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of dV/dt - dV/dt -		$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	200	V/µs	
		$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	500 ⁽¹⁾	v/µs	

Note

 $^{(1)}$ Available with dV/dt = 1000 V/µs, to complete code add S90 i.e. 50RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum, $t_p \le t$	5 ms	10	W
Maximum average gate power	P _{G(AV)}			2.5	vv
Maximum peak positive gate current	I _{GM}			2.5	А
Maximum peak positive gate voltage	+V _{GM}			20	V
Maximum peak negative gate voltage	-V _{GM}			10	v
	I _{GT}	T _J = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	250	mA
DC gate current required to trigger		T _J = 25 °C		100	
		T _J = 125 °C		50	
DC acts veltage required to triager	V	T _J = - 40 °C		3.5	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5	v
DC gate current not to trigger	I _{GD}	$T_J = T_J maximum,$ $V_{DRM} = Rated voltage$	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case	R _{thJC}			K/W
Maximum thermal resistance, case to heatsink	R _{thCS}			
		Non-lubricated threads	3.4 ^{+ 0 - 10} % (30)	N·m
Allowable mounting torque		Lubricated threads	2.3 ^{+ 0 - 10} % (20)	(lbf · in)
Approvimete weight			28	g
Approximate weight			1.0	oz.
Case style		See dimensions - link at the end of datasheet TO-208AC (C (TO-65)

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.078	0.057					
120°	0.094	0.098					
90°	0.120	0.130	$T_J = T_J maximum$	K/W			
60°	0.176	0.183					
30°	0.294	0.296					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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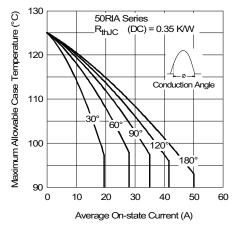


Fig. 1 - Current Ratings Characteristics

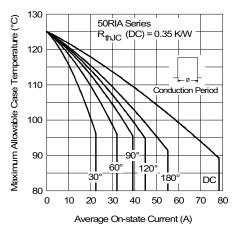


Fig. 2 - Current Ratings Characteristics

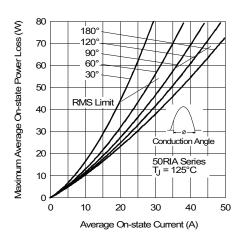


Fig. 3 - On-State Power Loss Characteristics

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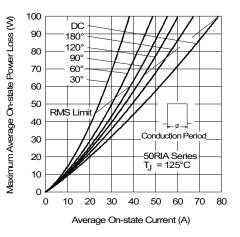


Fig. 4 - On-State Power Loss Characteristics

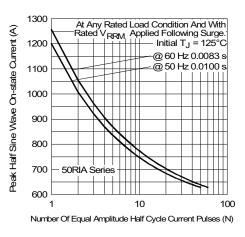


Fig. 5 - Maximum Non-Repetitive Surge Current

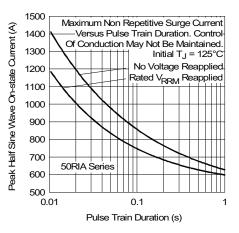


Fig. 6 - Maximum Non-Repetitive Surge Current

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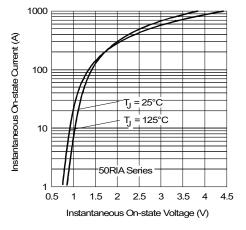


Fig. 7 - Forward Voltage Drop Characteristics

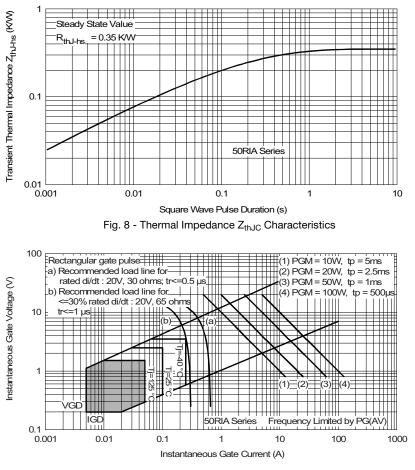
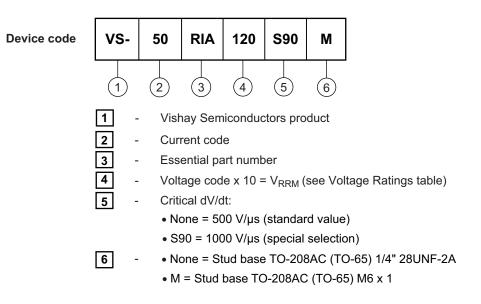


Fig. 9 - Gate Characteristics



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ORDERING INFORMATION TABLE



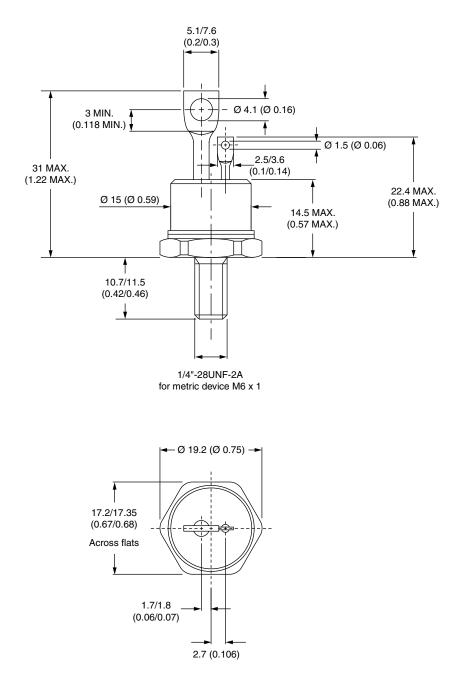
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95334		

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TO-208AC (TO-65)

DIMENSIONS in millimeters (inches)





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